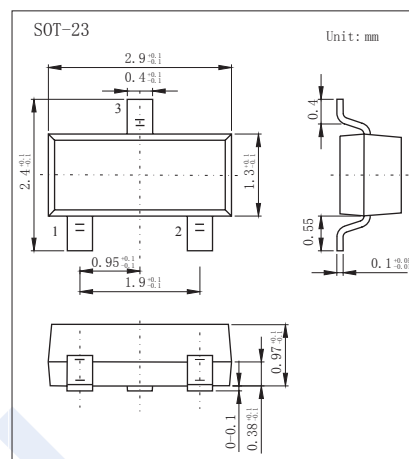
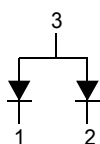


Switching Diodes

DAP202K (KAP202K)

■ Features

- Ultra high speed switching
- High reliability

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{RM}	80	V
Reverse Voltage (DC)	V_R	80	
Average rectified forward current (Single)	I_o	100	mA
Average rectified forward current (double)		150	
Forward Current (Single)	I_{FM}	300	
Forward Current (Double)		450	
Surge current ($t=1\mu\text{s}$) (Single)	I_{surge}	4	A
Surge current ($t=1\mu\text{s}$) (Double)		6	
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100\ \mu\text{A}$	80			V
Forward voltage	V_F	$I_F = 100\ \text{mA}$			1.2	
Reverse voltage leakage current	I_R	$V_R = 70\ \text{V}$			0.1	μA
Capacitance between terminals	C_t	$V_R = 6\ \text{V}, f = 1\ \text{MHz}$			3.5	pF
Reverse recovery time	t_{rr}	$V_R = 6\ \text{V}, I_F = 5\ \text{mA}, R_L = 50\ \Omega$			4	ns

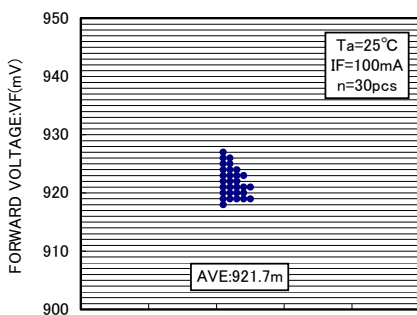
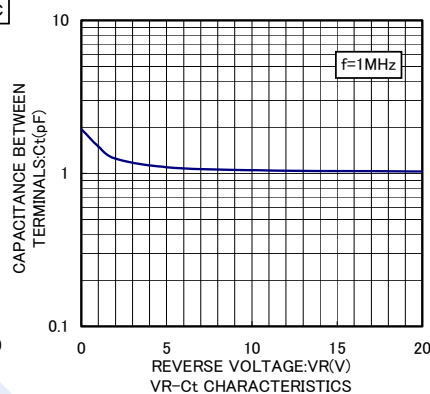
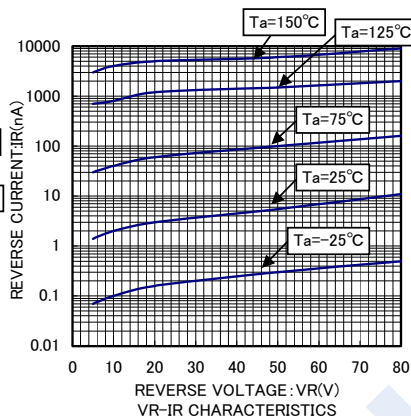
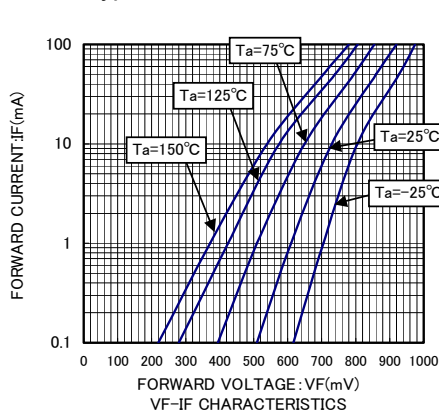
■ Marking

Marking	P*
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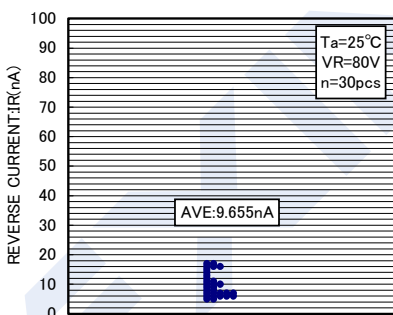
Switching Diodes

DAP202K (KAP202K)

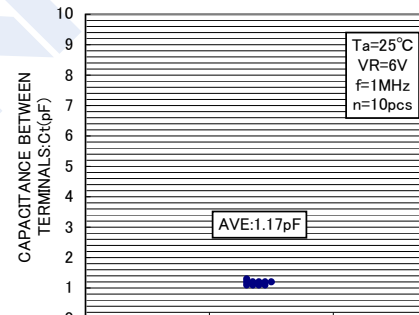
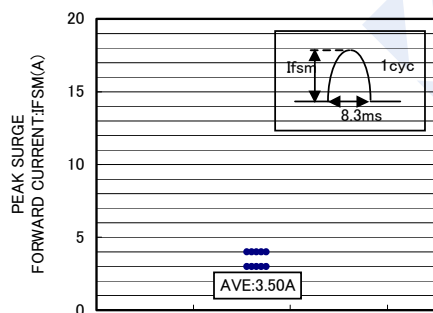
■ Typical Characteristics



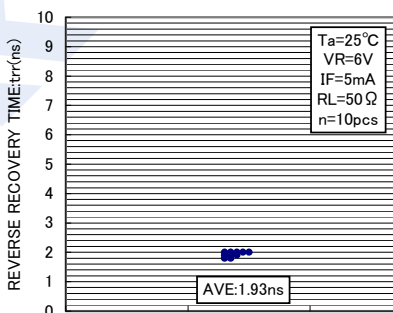
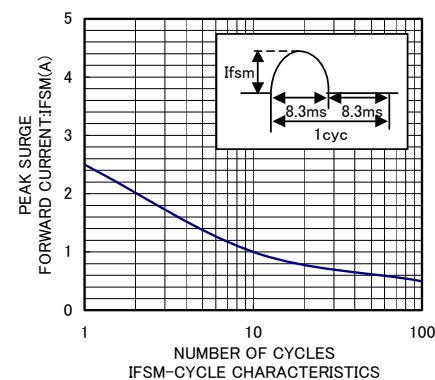
VF DISPERSION MAP



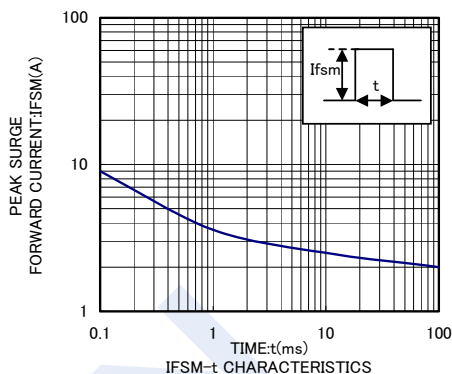
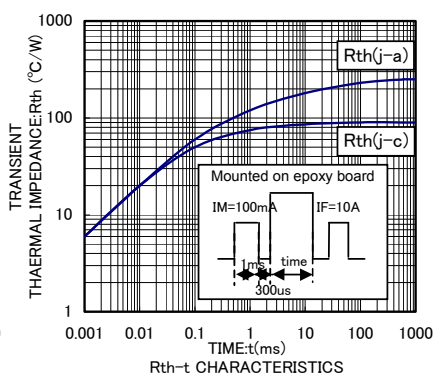
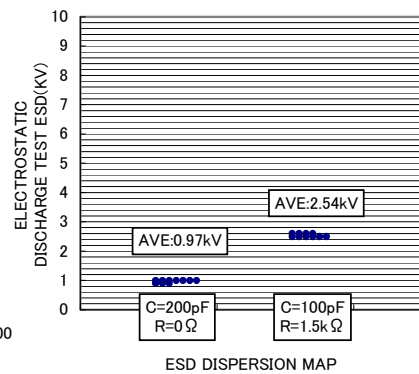
IR DISPERSION MAP

 C_t DISPERSION MAP

IFSM DISPERSION MAP

 t_{rr} DISPERSION MAP

IFSM-CYCLE CHARACTERISTICS

IFSM- t CHARACTERISTICS R_{th} - t CHARACTERISTICS

ESD DISPERSION MAP